

National Semiconductor Corporation

LF442A/LF442 Dual Low Power **JFET Input Operational Amplifier**

General Description

The LF442 dual low power operational amplifiers provide many of the same AC characteristics as the industry standard LM1458 while greatly improving the DC characteristics of the LM1458. The amplifiers have the same bandwidth. slew rate, and gain (10 k Ω load) as the LM1458 and only draw one tenth the supply current of the LM1458. In addition the well matched high voltage JFET input devices of the LF442 reduce the input bias and offset currents by a factor of 10,000 over the LM1458. A combination of careful layout design and internal trimming guarantees very low input offset voltage and voltage drift. The LF442 also has a very low equivalent input noise voltage for a low power amplifier.

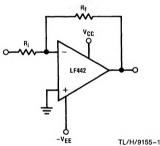
The LF442 is pin compatible with the LM1458 allowing an immediate 10 times reduction in power drain in many applications. The LF442 should be used where low power dissipation and good electrical characteristics are the major considerations.

Features

- 1/10 supply current of a LM1458
- Low input bias current
- Low input offset voltage Low input offset voltage drift
- High gain bandwidth
- High slew rate
- Low noise voltage for low power
- Low input noise current
- High input impedance
- High gain $V_0 = \pm 10V$, $R_L = 10k$

- 400 µA (max) 50 pA (max)
 - 1 mV (max)
 - 10 µV/°C (max)
 - 1 MHz
 - 1 V/us35 nV/√Hz
 - 0.01 pA/JHz
 - 10¹²Ω
 - 50k (min)



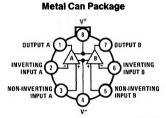


Simplified Schematic

Ordering Information LF442XYZ

- X indicates electrical grade
- indicates temperature range "M" for military "C" for commercial
- Z indicates package type "H" or "N"

Connection Diagrams

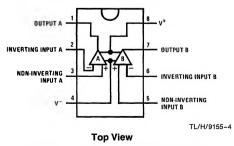


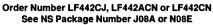
TL/H/9155-2

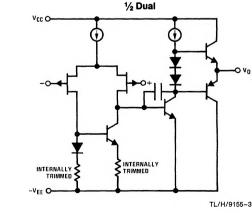
Top View Note: Pin 4 connected to case

Order Number LF442AMH, LF442ACH or LF442CH See NS Package Number H08B

Dual-In-Line Package







BI-FET IITM Technology

Absolute Maximum Ratings

If Military/Aerospace specified devices are required, contact the National Semiconductor Sales Office/ Distributors for availability and specifications. (Note 9)

	LF442A	LF442
Supply Voltage	±22V	±18V
Differential Input Voltage	±38V	±30V
Input Voltage Range (Note 1)	±19V	±15V
Output Short Circuit Duration (Note 2)	Continuous	Continuous

T _i max	H Package 150°C	N Package 115°C
θ_{JA} (Typical)		
(Note 3)	83°C/W	114°C/W
(Note 4)	217°C/W	152°C/W
$\theta_{\rm JC}$ (Typical)	21°C/W	
Operating Temperature Range	(Note 4)	(Note 4)
Storage Temperature Range	–65°C≤T _A ≤150°C	−65°C≤T _A ≤150°C
Lead Temperature (Soldering, 10 seconds)	260°C	260°C
ESD rating to be determine	ed.	

DC Electrical Characteristics (Note 6)

Symbol P	Parameter	Parameter Conditio	ons	LF442A				Units		
Symbol	r ai aiiititi	Conditions		Min	Тур	Max	Min	Тур	Max	
V _{OS}	Input Offset Voltage	$R_{\rm S} = 10 {\rm k}\Omega, T_{\rm A} = 25^{\circ}{\rm C}$			0.5	1.0		1.0	5.0	m٧
		Over Temperature							7.5	mV
ΔV _{OS} /ΔT	Average TC of Input Offset Voltage	$R_{S} = 10 \text{ k}\Omega$			7	10		7		μV/ºC
los	Input Offset Current	ut Offset Current $V_S = \pm 15V$ (Notes 6 and 7)	T _j = 25°C		5	25		5	50	pА
			T _j = 70°C			1.5			1.5	nA
			T _j = 125°C			10				nA
IB		$V_S = \pm 15V$ (Notes 6 and 7)	T _j = 25°C		10	50		10	100	pА
			$T_j = 70^{\circ}C$			3			3	nA
			T _j = 125°C			20				nA
R _{IN}	Input Resistance	T _j = 25°C			1012			1012		Ω
A _{VOL} Large Signal Voltage Gain	$V_{S} = \pm 15V, V_{O}$ $R_{L} = 10 \text{ k}\Omega, T_{A}$		50	200		25	200		V/mV	
		Over Temperatur	e	25	200		15	200		V/mV
vo	Output Voltage Swing	$V_{S} = \pm 15 V, R_{L}$	= 10 kΩ	±12	±13		±12	±13		v
V _{CM}	Input Common-Mode Voltage Range			±16	+ 18 - 17		±11	+ 14 - 12		v v
CMRR	Common-Mode Rejection Ratio	R _S ≤ 10 kΩ		80	100		70	95		dB
PSRR	Supply Voltage Rejection Ratio	(Note 8)		80	100		70	90		dB
Is	Supply Current				300	400		400	500	μA

AC Electrical Characteristics (Note 6)

Symbol	Parameter	Conditions	LF442A			LF442			Units
			Min	Тур	Max	Min	Тур	Max	Olinta
	Amplifier to Amplifier Coupling	$T_A = 25^{\circ}C$, f = 1 Hz-20 kHz (Input Referred)		- 120			- 120		dB
SR	Slew Rate	$V_{S} = \pm 15V, T_{A} = 25^{\circ}C$	0.8	1		0.6	1		V/µs
GBW	Gain-Bandwidth Product	$V_{S} = \pm 15V, T_{A} = 25^{\circ}C$	0.8	1		0.6	1		MHz
en	Equivalent Input Noise Voltage	$T_A = 25^{\circ}C, R_S = 100\Omega,$ f = 1 kHz		35			35		nV/√Hz
'n	Equivalent Input Noise Current	$T_A = 25^{\circ}C, f = 1 \text{ kHz}$		0.01			0.01		pA/√Hz

Note 1: Unless otherwise specified the absolute maximum negative input voltage is equal to the negative power supply voltage.

Note 2: Any of the amplifier outputs can be shorted to ground indefinitely, however, more than one should not be simultaneously shorted as the maximum junction temperature will be exceeded.

Note 3: The value given is in 400 linear feet/min air flow.

Note 4: The value given is in static air.

F442A/LF442

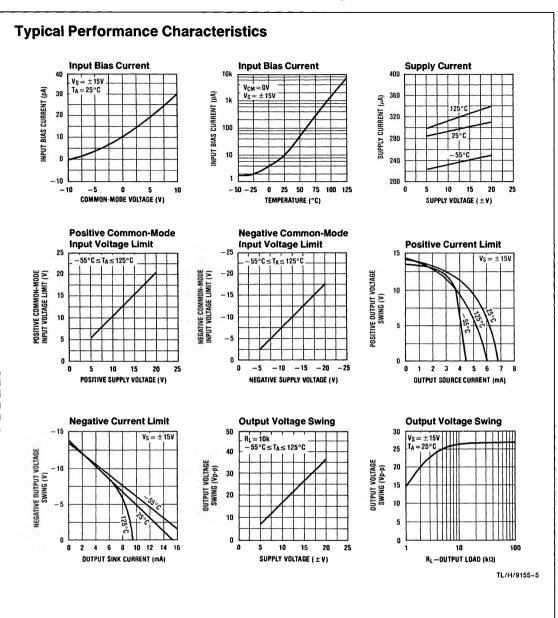
Note 5: These devices are available in both the commercial temperature range $0^{\circ}C \le T_A \le 70^{\circ}C$ and the military temperature range $-55^{\circ}C \le T_A \le 125^{\circ}C$. The temperature range is designated by the position just before the package type in the device number. A "C" indicates the commercial temperature range and an "M" indicates the military temperature range. The military temperature range is available in "H" package only.

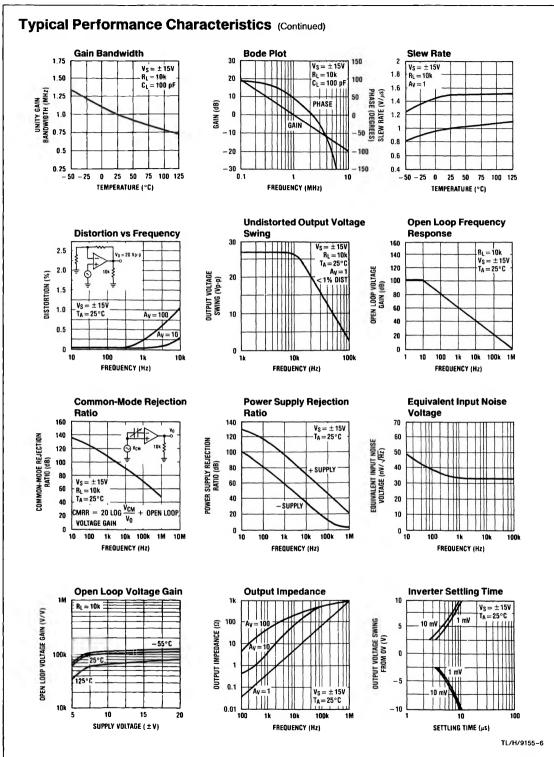
Note 6: Unless otherwise specified, the specifications apply over the full temperature range and for $V_S = \pm 20V$ for the LF442A and for $V_S = \pm 15V$ for the LF442. V_{OS} , I_B, and I_{OS} are measured at $V_{CM} = 0$.

Note 7: The input bias currents are junction leakage currents which approximately double for every 10°C increase in the junction temperature, T_j . Due to limited production test time, the input bias currents measured are correlated to junction temperature. In normal operation the junction temperature rises above the ambient temperature as a result of internal power dissipation, PD. $T_j = T_A + \theta_j A^p D$ where $\theta_j A$ is the thermal resistance from junction to ambient. Use of a heat sink is recommended if input bias current is to be kept to a minimum.

Note 8: Supply voltage rejection ratio is measured for both supply magnitudes increasing or decreasing simultaneously in accordance with common practice from ±15V to ±5V for the LF442 and ±20V to ±5V for the LF442A.

Note 9: Refer to RETS442AX for LF442AMH military specifications and to RETS442X for LF442MH military specifications.



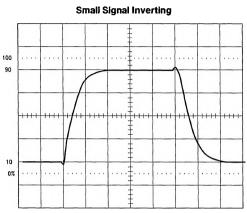


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LF442A/LF442

LF442A/LF442

Pulse Response R_L = 10 k\Omega, C_L = 10 pF

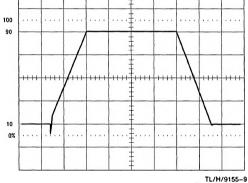


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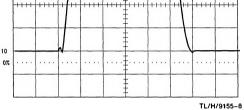
100

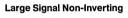
90

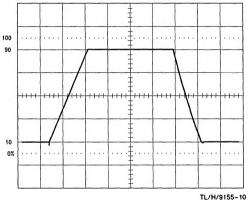




Small Signal Non-Inverting







Application Hints

This device is a dual low power op amp with internally trimmed input offset voltages and JFET input devices (BI-FET II). These JFETs have large reverse breakdown voltages from gate to source and drain eliminating the need for clamps across the inputs. Therefore, large differential input voltages can easily be accommodated without a large increase in input current. The maximum differential input voltage is independent of the supply voltages. However, neither of the input voltages should be allowed to exceed the negative supply as this will cause large currents to flow which can result in a destroyed unit.

Exceeding the negative common-mode limit on either input will force the output to a high state, potentially causing a reversal of phase to the output. Exceeding the negative common-mode limit on both inputs will force the amplifier output to a high state. In neither case does a latch occur since raising the input back within the common-mode range again puts the input stage and thus the amplifier in a normal operating mode.

Exceeding the positive common-mode limit on a single input will not change the phase of the output; however, if both inputs exceed the limit, the output of the amplifier will be forced to a high state.

The amplifiers will operate with a common-mode input voltage equal to the positive supply; however, the gain bandwidth and slew rate may be decreased in this condition. When the negative common-mode voltage swings to within 3V of the negative supply, an increase in input offset voltage may occur.

Each amplifier is individually biased to allow normal circuit operation with power supplies of $\pm 3.0V$. Supply voltages less than these may degrade the common-mode rejection and restrict the output voltage swing.

The amplifiers will drive a 10 k Ω load resistance to \pm 10V over the full temperature range.

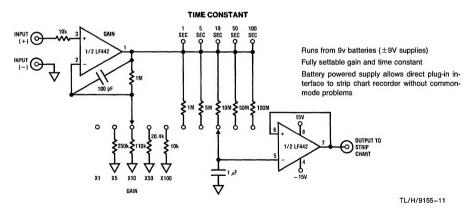
Precautions should be taken to ensure that the power supply for the integrated circuit never becomes reversed in polarity or that the unit is not inadvertently installed backwards in a socket as an unlimited current surge through the resulting forward diode within the IC could cause fusing of the internal conductors and result in a destroyed unit.

Because these amplifiers are JFET rather than MOSFET input op amps they do not require special handling.

As with most amplifiers, care should be taken with lead dress, component placement and supply decoupling in order to ensure stability. For example, resistors from the output to an input should be placed with the body close to the input to minimize "pick-up" and maximize the frequency of the feedback pole by minimizing the capacitance from the input to ground.

A feedback pole is created when the feedback around any amplifier is resistive. The parallel resistance and capacitance from the input of the device (usually the inverting input) to AC ground set the frequency of the pole. In many instances the frequency of this pole is much greater than the expected 3 dB frequency of the closed loop gain and consequenty there is negligible effect on stability margin. However, if the feedback pole is less than approximately 6 times the expected 3 dB frequency a lead capacitor should be placed from the output to the input of the op amp. The value of the added capacitor should be such that the RC time constant of this capacitor and the resistance it parallels is greater than or equal to the original feedback pole time constant.

Typical Applications



Battery Powered Strip Chart Preamplifier

Typical Applications (Continued)

"No FET" Low Power V \rightarrow F Converter UND TO THE STATE STAT

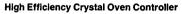
Trim 1M pot for 1 kHz full-scale output LF442A/LF442

15 mW power drain

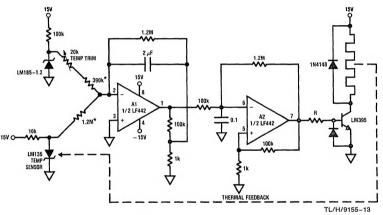
No integrator reset FET required Mount D1 and D2 in close proximity 1% linearity to 1 kHz

TL/H/9155-14

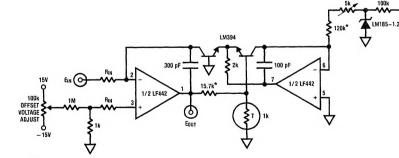
TL/H/9155-12



- T_{control} = 75°C
- A1's output represents the amplified difference between the LM335 temperature sensor and the crystal oven's temperature
- A2, a free running duty cycle modulator, drives the LM395 to complete a servo loop
- Switched mode operation yields high efficiency
- 1% metal film resistor



Conventional Log Amplifier



 $E_{OUT} = -\left[\log 10 \left(\frac{E_{IN}}{R_{IN}}\right) + 5\right]$ R_T = Tel Labs type Q81

Trim 5k for 10 μ A through the 5k-120k combination *1% film resistor

LF442A/LF442

Typical Applications (Continued) Q1, Q2, Q3 are included on LM389 Unconventional Log Amplifier amplifier chip which is temperaturestabilized by the LM389 and Q2-Q3, which act as a heater-sensor pair. 12V Q1, the logging transistor, is thus im-LM340L-12 mune to ambient temperature variation and requires no temperature \diamond 1k compensation at all. 10k 100k Scale Factor LM329 10k ADJUST 01 12 I M380 02 15V Q 17 1N914 2.2k 2N2907 \$ 27 1k ٤ 1/2 LF442 -0 2k* OUTPUT 4 **0-10V FOR INPUTS** 300 nF γ 03 OF 10 nA-1 mA 10 151 15 12V C 2 I LOG INPUT O 1/2 LF442 E LOG INPUT C 15V 10M C 50k ZERO ADJUST 15\ TL/H/9155-15



